Ordering number : ENA0444

SANYO Semiconductors
DATA SHEET

SB10015M — Low I_R Schottky Barrier Diode 15V, 1.0A Rectifier

Applications

- High frequency rectification (switching regulators, converters, choppers).

Features

- Small switching noise.
- Low leakage current and high reliability due to highly reliable planar structure.
- Ultrasmall package permitting applied sets to be small and slim (mounting height 0.85mm).

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Repetitive Peak Reverse Voltage	V_{RRM}		15	V
Nonrepetitive Peak Reverse Surge Voltage	V_{RSM}		17	V
Average Output Current	I_O		1.0	A
Surge Forward Current	I_{FSM}	50Hz sine wave, 1 cycle	10	A
Junction Temperature	Tj		−55 to +150	°C
Storage Temperature	Tstg		−55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Reverse Voltage	V_R	I_R=0.1mA	15			V
Forward Voltage	V_F1	I_F=0.5A		0.43	0.48	V
	V_F2	I_F=1.0A		0.49	0.54	V
Reverse Current	I_R	V_R=7.5V			3	μA
Interterminal Capacitance	C	V_R=10V, f=1MHz		20		pF
Reverse Recovery Time	t_{rr}	I_F=I_R=100mA, See specified Test Circuit.			10	ns
Therrmal Resistance	Rth(j-a)	Mounted in Cu-foiled area of 0.72mm²×0.03mm on glass epoxy board		185		°C / W

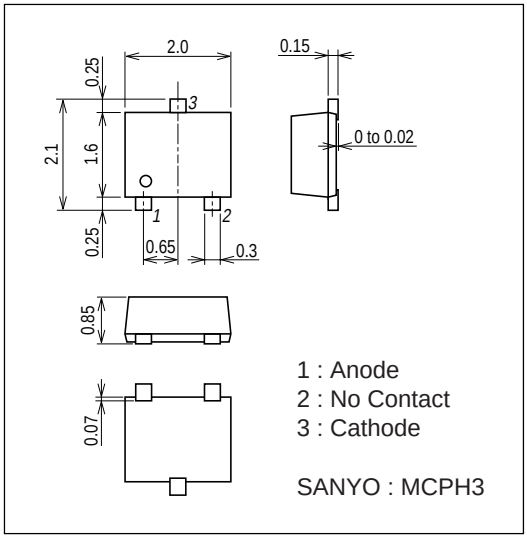
Marking : SL

SANYO Semiconductor Co., Ltd.
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

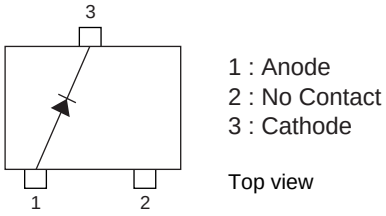
Package Dimensions

unit : mm (typ)

7019A-001



Electrical Connection



t_{rr} Test Circuit